

60 µA, High Precision Op Amps

Features

- Low Offset Voltage: ±150 μV (maximum)
- Low Quiescent Current: 60 µA (typical)
- Rail-to-Rail Input and Output
- Wide Supply Voltage Range: 1.8V to 6.0V
- Gain Bandwidth Product: 730 kHz (typical)
- · Unity Gain Stable
- Extended Temperature Range: -40°C to +125°C
- No Phase Reversal

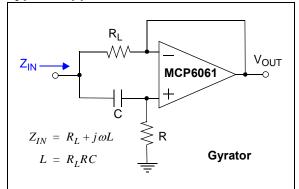
Applications

- Automotive
- Portable Instrumentation •
- Sensor Conditioning
- Battery Powered Systems
- Medical Instrumentation
- **Test Equipment** ٠
- Analog Filters

Design Aids

- SPICE Macro Models
- FilterLab[®] Software
- Microchip Advanced Part Selector (MAPS)
- ٠ Analog Demonstration and Evaluation Boards
- Application Notes

Typical Application



Description

The Microchip Technology Inc. MCP6061/2/4 family of operational amplifiers (op amps) has low input offset voltage (±150 µV, maximum) and rail-to-rail input and output operation. This family is unity gain stable and has a gain bandwidth product of 730 kHz (typical). These devices operate with a single supply voltage as low as 1.8V, while drawing low quiescent current per amplifier (60 µA, typical). These features make the family of op amps well suited for single-supply, high precision, battery-powered applications.

The MCP6061/2/4 family is offered in single (MCP6061), dual (MCP6062), and quad (MCP6064) configurations.

The MCP6061/2/4 is designed with Microchip's advanced CMOS process. All devices are available in the extended temperature range, with a power supply range of 1.8V to 6.0V.

MCP6062 MCP6061 SOIC SOIC 8 NC NC 1 V_{OUTA} 1 7 V_{DD} V_{INA}– 2 $V_{IN} - 2$ V_{IN}+3 6 V_{OUT} V_{INA}+ 3 V_{SS} 4 5 NC V_{SS} 4

MCP6061 2x3 TDFN *

VOUT

8

ΕP

9

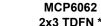
MCP6061

SOT-23-5

7

6

5 NC

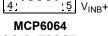




ર

V_{INA}+

V_{SS}



9

8 V_{DD}

7 V_{OUTB}

6 V_{INB}-

5 V_{INB}+

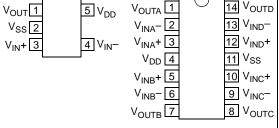
 V_{DD}

V_{OUTB}

V_{INB}-

6

SOIC, TSSOP



* Includes Exposed Thermal Pad (EP); see Table 3-1.

Package Types

1 0

2

3

NC

VIN-

V_{IN}+

 V_{SS} 4

NOTES:

1.0 ELECTRICAL CHARACTERISTICS

1.1 Absolute Maximum Ratings †

V _{DD} – V _{SS}
Current at Input Pins±2 mA
Analog Inputs (V_IN+, V_IN-)†† V_SS – 1.0V to V_DD + 1.0V
All Other Inputs and Outputs V_{SS} – 0.3V to V_{DD} + 0.3V
Difference Input Voltage $ V_{DD} - V_{SS} $
Output Short-Circuit Currentcontinuous
Current at Output and Supply Pins±30 mA
Storage Temperature65°C to +150°C
Maximum Junction Temperature (T _J)+150°C
ESD protection on all pins (HBM; MM) \geq 4 kV; 400V

† Notice: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

†† See **4.1.2 "Input Voltage Limits**"

1.2 Specifications

DC ELECTRICAL SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated, $V_{DD} = +1.8V$ to +6.0V, $V_{SS} = GND$, $T_A = +25^{\circ}C$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $V_L = V_{DD}/2$ and $R_L = 10 \text{ k}\Omega$ to V_L . (Refer to Figure 1-1).

Parameters	Sym	Min	Тур	Max	Units	Conditions
Input Offset		•		•		
Input Offset Voltage	V _{OS}	-150	_	+150	μV	$V_{DD} = 3.0V,$ $V_{CM} = V_{DD}/3$
Input Offset Drift with Temperature	$\Delta V_{OS} / \Delta T_A$	—	±1.5	—	µV/°C	T_A = -40°C to +85°C, V _{DD} = 3.0V, V _{CM} = V _{DD} /3
	$\Delta V_{OS} / \Delta T_A$	—	±4.0	—	µV/°C	T_A = +85°C to +125°C, V _{DD} = 3.0V, V _{CM} = V _{DD} /3
Power Supply Rejection Ratio	PSRR	70	87	—	dB	$V_{CM} = V_{SS}$
Input Bias Current and Impedance						
Input Bias Current	Ι _Β	—	±1.0	100	pА	
	I _B	—	60	—	pА	T _A = +85°C
	I _B	—	1100	5000	pА	T _A = +125°C
Input Offset Current	I _{OS}	—	±1.0	—	pА	
Common Mode Input Impedance	Z _{CM}	—	10 ¹³ 6	—	ΩpF	
Differential Input Impedance	Z _{DIFF}	—	10 ¹³ 6	—	Ω pF	
Common Mode						
Common Mode Input Voltage Range	V _{CMR}	V _{SS} -0.15	-	V _{DD} +0.15	V	V _{DD} = 1.8V (Note 1)
	V _{CMR}	V _{SS} -0.3		V _{DD} +0.3	V	V _{DD} = 6.0V (Note 1)
Common Mode Rejection Ratio	CMRR	72	89	—	dB	$V_{CM} = -0.15V$ to 1.95V, $V_{DD} = 1.8V$
		74	91	—	dB	$V_{CM} = -0.3V$ to 6.3V, $V_{DD} = 6.0V$
		72	87	—	dB	$V_{CM} = 3.0V$ to 6.3V, $V_{DD} = 6.0V$
		74	89	—	dB	$V_{CM} = -0.3V$ to 3.0V, $V_{DD} = 6.0V$

Note 1: Figure 2-13 shows how V_{CMR} changed across temperature.

DC ELECTRICAL SPECIFICATIONS (CONTINUED)

Electrical Characteristics : Unless otherwise indicated, $V_{DD} = +1.8V$ to +6.0V, $V_{SS} = GND$, $T_A = +25^{\circ}C$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $V_L = V_{DD}/2$ and $R_L = 10 \text{ k}\Omega$ to V_L . (Refer to Figure 1-1).							
Parameters	Sym	Min	Тур	Max	Units	Conditions	
Open-Loop Gain							
DC Open-Loop Gain (Large Signal)	A _{OL}	95	115 — dB $0.2V < V_{OUT} < (V_{DD}-0.2V)$ $V_{CM} = V_{SS}$				
Output							
Maximum Output Voltage Swing	V _{OL,} V _{OH}	V _{SS} +15		V _{DD} -15	mV	0.5V input overdrive	
Output Short-Circuit Current	I _{SC}	_	±6	—	mA	V _{DD} = 1.8V	
		—	±27	—	mA	V _{DD} = 6.0V	
Power Supply							
Supply Voltage	V _{DD}	1.8		6.0	V		
Quiescent Current per Amplifier	Ι _Q	30	60	90	μA	$\begin{split} I_{O} &= 0, \ V_{DD} = 6.0 V \\ V_{CM} &= 0.9 V_{DD} \end{split}$	

Note 1: Figure 2-13 shows how V_{CMR} changed across temperature.

AC ELECTRICAL SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8$ to +6.0V, $V_{SS} = GND$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 60 \text{ pF}$. (Refer to Figure 1-1).

Parameters	Sym	Min	Тур	Мах	Units	Conditions
AC Response						
Gain Bandwidth Product	GBWP	_	730	_	kHz	
Phase Margin	PM	_	61	_	0	G = +1 V/V
Slew Rate	SR	_	0.25	_	V/µs	
Noise						
Input Noise Voltage	E _{ni}	_	4.5	_	µVp-p	f = 0.1 Hz to 10 Hz
Input Noise Voltage Density	e _{ni}	_	25	_	nV/√Hz	f = 10 kHz
Input Noise Current Density	i _{ni}	_	0.6	_	fA/√Hz	f = 1 kHz

TEMPERATURE SPECIFICATIONS

Electrical Characteristics: Unless otherwise indicated, V_{DD} = +1.8V to +6.0V and V_{SS} = GND.								
Parameters	Sym	Min	Тур	Max	Units	Conditions		
Temperature Ranges								
Operating Temperature Range	T _A	-40	—	+125	°C	Note 1		
Storage Temperature Range	T _A	-65	_	+150	°C			
Thermal Package Resistances		•						
Thermal Resistance, 5L-SOT-23	θ_{JA}	_	220.7	_	°C/W			
Thermal Resistance, 8L-2x3 TDFN	θ_{JA}	_	52.5	_	°C/W			
Thermal Resistance, 8L-SOIC	θ_{JA}	_	149.5	—	°C/W			
Thermal Resistance, 14L-SOIC	θ_{JA}	—	95.3		°C/W			
Thermal Resistance, 14L-TSSOP	θ _{JA}	—	100	—	°C/W			

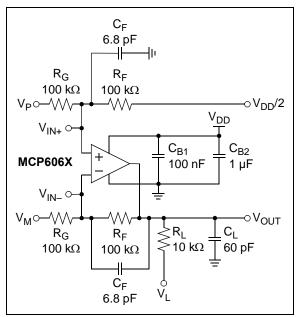
Note 1: The internal junction temperature (T_J) must not exceed the absolute maximum specification of +150°C.

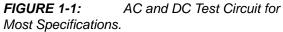
1.3 Test Circuits

The circuit used for most DC and AC tests is shown in Figure 1-1. This circuit can independently set V_{CM} and V_{OUT}; see Equation 1-1. Note that V_{CM} is not the circuit's common mode voltage ((V_P + V_M)/2), and that V_{OST} includes V_{OS} plus the effects (on the input offset error, V_{OST}) of temperature, CMRR, PSRR and A_{OL}.

EQUATION 1-1:

$$\begin{split} G_{DM} &= R_F / R_G \\ V_{CM} &= (V_P + V_{DD} / 2) / 2 \\ V_{OST} &= V_{IN-} - V_{IN+} \\ V_{OUT} &= (V_{DD} / 2) + (V_P - V_M) + V_{OST} (I + G_{DM}) \\ \end{split}$$
Where:
$$\begin{split} G_{DM} &= \text{Differential Mode Gain} \qquad (V/V) \\ V_{CM} &= \text{Op Amp's Common Mode} \qquad (V) \\ \text{Input Voltage} \\ V_{OST} &= \text{Op Amp's Total Input Offset} \qquad (mV) \\ \text{Voltage} \end{split}$$





NOTES:

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to +6.0V, $V_{SS} = GND$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 60 \text{ pF}$.

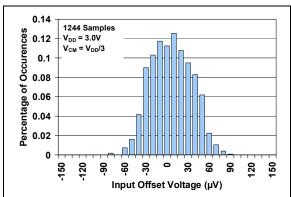


FIGURE 2-1: Input Offset Voltage with $V_{DD} = 3.0V$.

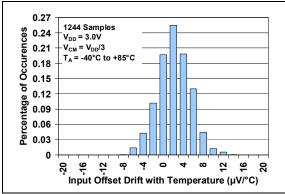


FIGURE 2-2: Input Offset Voltage Drift with $V_{DD} = 3.0V$ and $T_A \le +85^{\circ}C$.

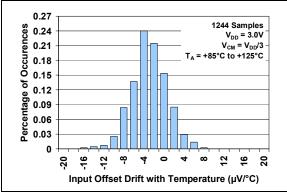


FIGURE 2-3: Input Offset Voltage Drift with $V_{DD} = 3.0V$ and $T_A \ge +85^{\circ}C$.

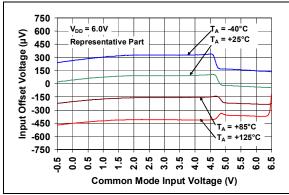


FIGURE 2-4: Input Offset Voltage vs. Common Mode Input Voltage with $V_{DD} = 6.0V$.

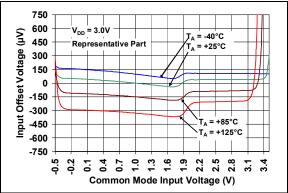


FIGURE 2-5: Input Offset Voltage vs. Common Mode Input Voltage with $V_{DD} = 3.0V$.

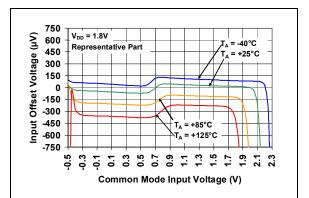
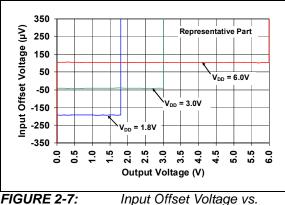


FIGURE 2-6: Input Offset Voltage vs. Common Mode Input Voltage with $V_{DD} = 1.8V$.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to +6.0V, $V_{SS} = GND$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 60 \text{ pF}$.





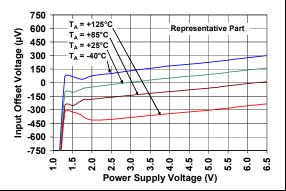
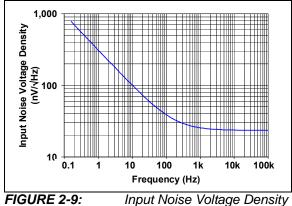


FIGURE 2-8: Input Offset Voltage vs. Power Supply Voltage.



vs. Frequency.

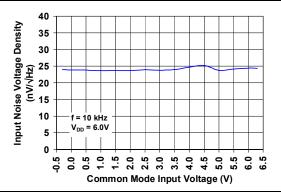


FIGURE 2-10: Input Noise Voltage Density vs. Common Mode Input Voltage.

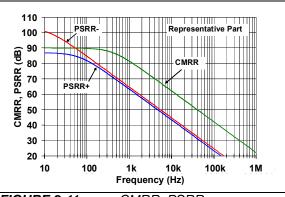


FIGURE 2-11: CMRR, PSRR vs. Frequency.

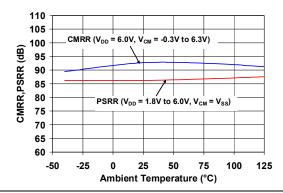


FIGURE 2-12:CMRR, PSRR vs. AmbientTemperature.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to +6.0V, $V_{SS} = GND$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 60 \text{ pF}$.

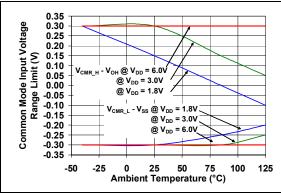


FIGURE 2-13: Common Mode Input Voltage Range Limit vs. Ambient Temperature.

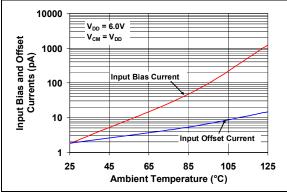


FIGURE 2-14: Input Bias, Offset Currents vs. Ambient Temperature.

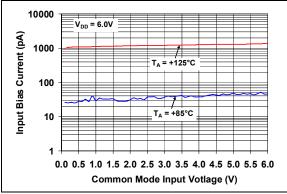


FIGURE 2-15: Input Bias Current vs. Common Mode Input Voltage.

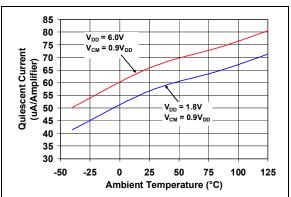


FIGURE 2-16: Quiescent Current vs Ambient Temperature with $V_{CM} = 0.9V_{DD}$.

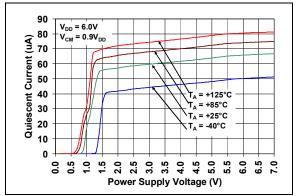
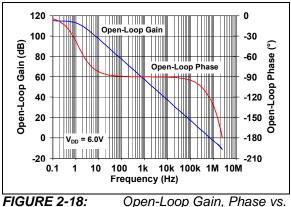


FIGURE 2-17: Quiescent Current vs. Power Supply Voltage with $V_{CM} = 0.9V_{DD}$.



Frequency.

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Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to +6.0V, $V_{SS} = GND$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 60 \text{ pF}$.

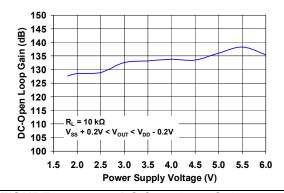


FIGURE 2-19: DC Open-Loop Gain vs. Power Supply Voltage.

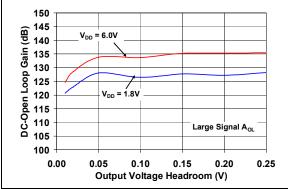


FIGURE 2-20: DC Open-Loop Gain vs. Output Voltage Headroom.

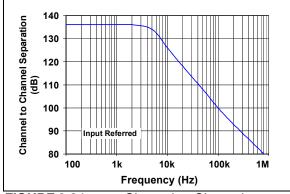


FIGURE 2-21: Channel-to-Channel Separation vs. Frequency (MCP6062/4 only).

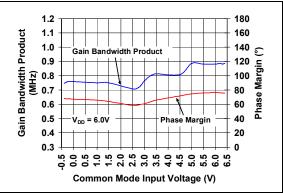


FIGURE 2-22: Gain Bandwidth Product, Phase Margin vs. Common Mode Input Voltage.

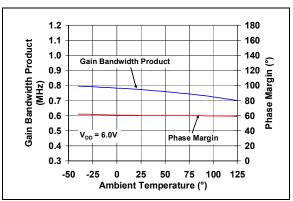


FIGURE 2-23: Gain Bandwidth Product, Phase Margin vs. Ambient Temperature.

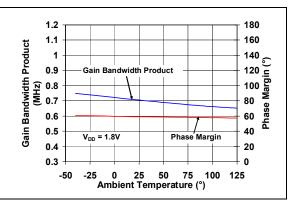


FIGURE 2-24: Gain Bandwidth Product, Phase Margin vs. Ambient Temperature.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to +6.0V, $V_{SS} = GND$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 60 \text{ pF}$.

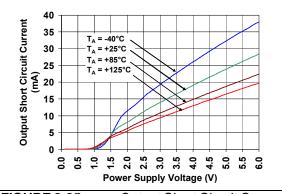
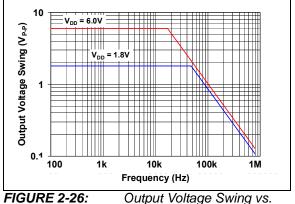


FIGURE 2-25: Output Short Circuit Current vs. Power Supply Voltage.



Frequency.

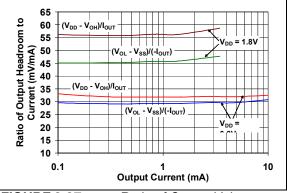


FIGURE 2-27: Ratio of Output Voltage Headroom to Output Current vs. Output Current.

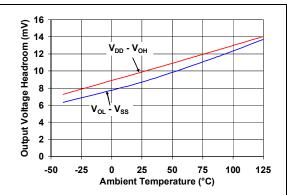


FIGURE 2-28: Output Voltage Headroom vs. Ambient Temperature.

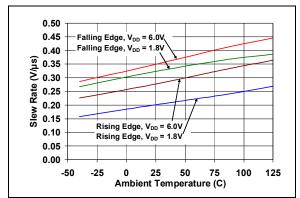
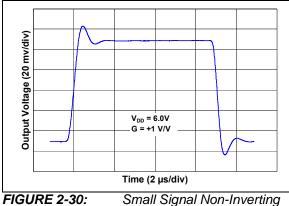


FIGURE 2-29: Slew Rate vs. Ambient Temperature.



Pulse Response.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$, $V_{DD} = +1.8V$ to +6.0V, $V_{SS} = GND$, $V_{CM} = V_{DD}/2$, $V_{OUT} \approx V_{DD}/2$, $V_L = V_{DD}/2$, $R_L = 10 \text{ k}\Omega$ to V_L and $C_L = 60 \text{ pF}$.

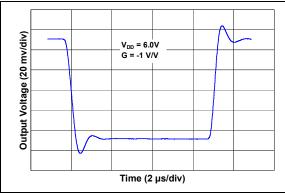


FIGURE 2-31: Small Signal Inverting Pulse Response.

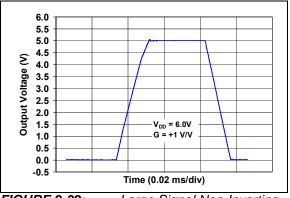
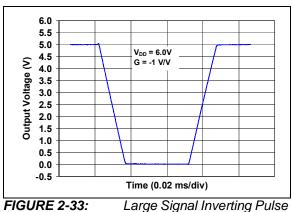


FIGURE 2-32: Large Signal Non-Inverting Pulse Response.



Response.

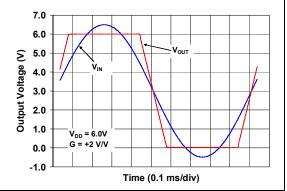


FIGURE 2-34: The MCP6061/2/4 Shows No Phase Reversal.

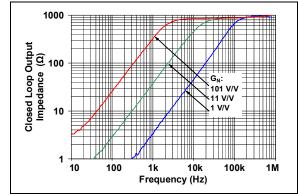


FIGURE 2-35: Closed Loop Output Impedance vs. Frequency.

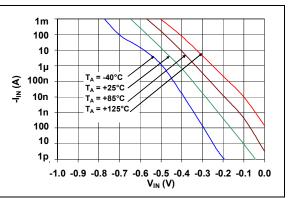


FIGURE 2-36: Measured Input Current vs. Input Voltage (below V_{SS}).

3.0 PIN DESCRIPTIONS

Descriptions of the pins are listed in Table 3-1.

	MCP6061		MCP6062		MCP6064		
SOIC	SOT-23-5	2x3 TDFN	SOIC	2x3 TDFN	SOIC, TSSOP	Symbol	Description
6	1	6	1	1	1	V _{OUT} , V _{OUTA}	Analog Output (op amp A)
2	4	2	2	2	2	V _{IN} —, V _{INA} —	Inverting Input (op amp A)
3	3	3	3	3	3	V _{IN} +, V _{INA} +	Non-inverting Input (op amp A)
7	5	7	8	8	4	V _{DD}	Positive Power Supply
_	—	_	5	5	5	V _{INB} +	Non-inverting Input (op amp B)
_	—	_	6	6	6	V _{INB} -	Inverting Input (op amp B)
_	_	_	7	7	7	V _{OUTB}	Analog Output (op amp B)
_	—	_	_	—	8	V _{OUTC}	Analog Output (op amp C)
_	—	_	_	—	9	V _{INC} -	Inverting Input (op amp C)
_	—	_	_	—	10	V _{INC} +	Non-inverting Input (op amp C)
4	2	4	4	4	11	V _{SS}	Negative Power Supply
_	—	_	_	—	12	V _{IND} +	Non-inverting Input (op amp D)
_	—	_	_	—	13	V _{IND} -	Inverting Input (op amp D)
_	_	_	_	_	14	V _{OUTD}	Analog Output (op amp D)
1, 5, 8	_	1, 5, 8	_	_	_	NC	No Internal Connection
—	—	9	_	9	—	EP	Exposed Thermal Pad (EP); must be connected to V _{SS} .

TABLE 3-1: PIN FUNCTION TABLE

3.1 Analog Outputs

The output pins are low-impedance voltage sources.

3.2 Analog Inputs

The non-inverting and inverting inputs are highimpedance CMOS inputs with low bias currents.

3.3 Power Supply Pins

The positive power supply (V_{DD}) is 1.8V to 6.0V higher than the negative power supply (V_{SS}). For normal operation, the other pins are at voltages between V_{SS} and V_{DD}.

Typically, these parts are used in a single (positive) supply configuration. In this case, V_{SS} is connected to ground and V_{DD} is connected to the supply. V_{DD} will need bypass capacitors.

3.4 Exposed Thermal Pad (EP)

There is an internal electrical connection between the Exposed Thermal Pad (EP) and the V_{SS} pin; they must be connected to the same potential on the Printed Circuit Board (PCB).Frequency (Hz)

NOTES:

4.0 APPLICATION INFORMATION

The MCP6061/2/4 family of op amps is manufactured using Microchip's state-of-the-art CMOS process and is specifically designed for low-power, high precision applications.

4.1 Rail-to-Rail Input

4.1.1 PHASE REVERSAL

The MCP6061/2/4 op amps are designed to prevent phase reversal when the input pins exceed the supply voltages. Figure 2-34 shows the input voltage exceeding the supply voltage without any phase reversal.

4.1.2 INPUT VOLTAGE LIMITS

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the voltages at the input pins (see Section 1.1 "Absolute Maximum Ratings †").

The ESD protection on the inputs can be depicted as shown in Figure 4-1. This structure was chosen to protect the input transistors and to minimize input bias current (I_B).

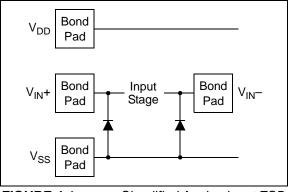


FIGURE 4-1: Structures.

Simplified Analog Input ESD

The input ESD diodes clamp the inputs when they try to go more than one diode drop below V_{SS} . They also clamp any voltages that go well above V_{DD} ; their breakdown voltage is high enough to allow normal operation, but not low enough to protect against slow over-voltage (beyond V_{DD}) events. Very fast ESD events (that meet the spec) are limited so that damage does not occur.

In some applications, it may be necessary to prevent excessive voltages from reaching the op amp inputs. Figure 4-2 shows one approach to protecting these inputs.

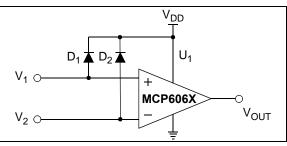


FIGURE 4-2: Protecting the Analog Inputs.

A significant amount of current can flow out of the inputs when the Common Mode voltage (V_{CM}) is below ground (V_{SS}). See Figure 2-36.

4.1.3 INPUT CURRENT LIMITS

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the voltages at the input pins (see Section 1.1 "Absolute Maximum Ratings †").

Figure 4-3 shows one approach to protecting these inputs. The resistors R_1 and R_2 limit the possible currents in or out of the input pins (and the ESD diodes, D_1 and D_2). The diode currents will go through either V_{DD} or V_{SS} .

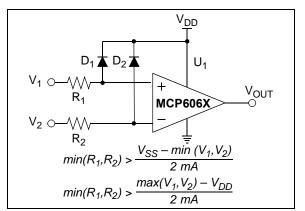


FIGURE 4-3: Protecting the Analog Inputs.

4.1.4 NORMAL OPERATION

The input stage of the MCP6061/2/4 op amps use two differential input stages in parallel. One operates at a low common mode input voltage (V_{CM}), while the other operates at a high V_{CM}. With this topology, the device operates with a V_{CM} up to 300 mV above V_{DD} and 300 mV below V_{SS}. (See Figure 2-13).The input offset voltage is measured at V_{CM} = V_{SS} - 0.3V and V_{DD} + 0.3V to ensure proper operation.

The transition between the input stages occurs when V_{CM} is near $V_{DD} - 1.1V$ (See Figures 2-4, 2-5 and Figure 2-6). For the best distortion performance and gain linearity, with non-inverting gains, avoid this region of operation.

4.2 Rail-to-Rail Output

The output voltage range of the MCP6061/2/4 op amps is V_{SS} + 15 mV (minimum) and V_{DD} – 15 mV (maximum) when R_L = 10 $k\Omega$ is connected to $V_{DD}/2$ and V_{DD} = 6.0V. Refer to Figures 2-27 and 2-28 for more information.

4.3 Capacitive Loads

Driving large capacitive loads can cause stability problems for voltage feedback op amps. As the load capacitance increases, the feedback loop's phase margin decreases and the closed-loop bandwidth is reduced. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. While a unity-gain buffer (G = +1) is the most sensitive to capacitive loads, all gains show the same general behavior.

When driving large capacitive loads with these op amps (e.g., > 100 pF when G = +1), a small series resistor at the output (R_{ISO} in Figure 4-4) improves the feedback loop's phase margin (stability) by making the output load resistive at higher frequencies. The bandwidth will be generally lower than the bandwidth with no capacitance load.

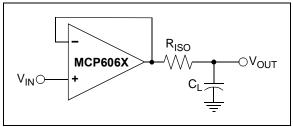


FIGURE 4-4: Output Resistor, R_{ISO} Stabilizes Large Capacitive Loads.

Figure 4-5 gives recommended R_{ISO} values for different capacitive loads and gains. The x-axis is the normalized load capacitance (C_L/G_N), where G_N is the circuit's noise gain. For non-inverting gains, G_N and the Signal Gain are equal. For inverting gains, G_N is 1+|Signal Gain| (e.g., -1 V/V gives $G_N = +2$ V/V).

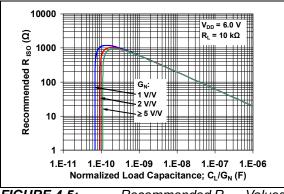


FIGURE 4-5: Recommended R_{ISO} Values for Capacitive Loads.

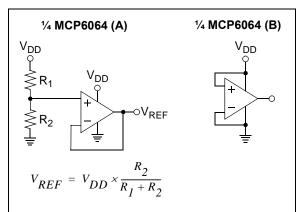
After selecting R_{ISO} for your circuit, double-check the resulting frequency response peaking and step response overshoot. Modify R_{ISO} 's value until the response is reasonable. Bench evaluation and simulations with the MCP6061/2/4 SPICE macro model are very helpful.

4.4 Supply Bypass

With this family of operational amplifiers, the power supply pin (V_{DD} for single-supply) should have a local bypass capacitor (i.e., 0.01 µF to 0.1 µF) within 2 mm for good high frequency performance. It can use a bulk capacitor (i.e., 1 µF or larger) within 100 mm to provide large, slow currents. This bulk capacitor can be shared with other analog parts.

4.5 Unused Op Amps

An unused op amp in a quad package (MCP6064) should be configured as shown in Figure 4-6. These circuits prevent the output from toggling and causing crosstalk. Circuit A sets the op amp at its minimum noise gain. The resistor divider produces any desired reference voltage within the output voltage range of the op amp; the op amp buffers that reference voltage. Circuit B uses the minimum number of components and operates as a comparator, but it may draw more current.





4.6 PCB Surface Leakage

In applications where low input bias current is critical, Printed Circuit Board (PCB) surface leakage effects need to be considered. Surface leakage is caused by humidity, dust or other contamination on the board. Under low humidity conditions, a typical resistance between nearby traces is $10^{12}\Omega$. A 5V difference would cause 5 pA of current to flow; which is greater than the MCP6061/2/4 family's bias current at +25°C (±1.0 pA, typical).

The easiest way to reduce surface leakage is to use a guard ring around sensitive pins (or traces). The guard ring is biased at the same voltage as the sensitive pin. An example of this type of layout is shown in Figure 4-7.

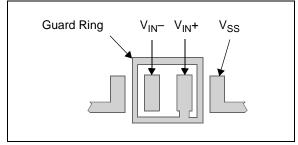


FIGURE 4-7: Example Guard Ring Layout for Inverting Gain.

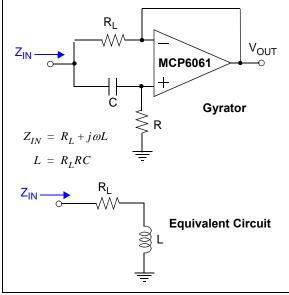
- 1. Non-inverting Gain and Unity-Gain Buffer:
 - a) Connect the non-inverting pin (V_{IN}+) to the input with a wire that does not touch the PCB surface.
 - b) Connect the guard ring to the inverting input pin (V_{IN}-). This biases the guard ring to the common mode input voltage.
- 2. Inverting Gain and Transimpedance Gain Amplifiers (convert current to voltage, such as photo detectors):
 - a) Connect the guard ring to the non-inverting input pin (V_{IN}+). This biases the guard ring to the same reference voltage as the op amp (e.g., V_{DD}/2 or ground).
 - b) Connect the inverting pin (V_{IN}-) to the input with a wire that does not touch the PCB surface.

4.7 Application Circuits

4.7.1 GYRATOR

The MCP6061/2/4 op amps can be used in gyrator applications. The gyrator is an electric circuit which can make a capacitive circuit behave inductively.

Figure 4-8 shows an example of a gyrator simulating inductance, with an approximately equivalent circuit below. The two $Z_{\rm IN}$ have similar values in typical applications. The primary application for a gyrator is to reduce the size and cost of a system by removing the need for bulky, heavy and expensive inductors. For example, RLC bandpass filter characteristics can be realized with capacitors, resistors and operational amplifiers without using inductors. Moreover, gyrators will typically have higher accuracy than real inductors, due to the lower cost of precision capacitors than inductors.



Gyrator.

FIGURE 4-8:

4.7.2 INSTRUMENTATION AMPLIFIER

The MCP6061/2/4 op amps are well suited for conditioning sensor signals in battery-powered applications. Figure 4-9 shows a two op amp instrumentation amplifier, using the MCP6062, that works well for applications requiring rejection of common mode noise at higher gains. The reference voltage (V_{REF}) is supplied by a low impedance source. In single supply applications, V_{REF} is typically $V_{DD}/2$.

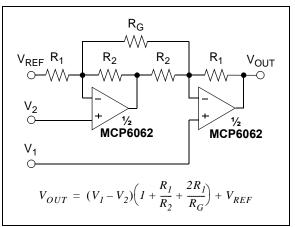


FIGURE 4-9: Two Op Amp Instrumentation Amplifier.

To obtain the best CMRR possible, and not limit the performance by the resistor tolerances, set a high gain with the R_G resistor.

4.7.3 PRECISION COMPARATOR

Use high gain before a comparator to improve the latter's input offset performance. Figure 4-10 shows a gain of 11 V/V placed before a comparator. The reference voltage V_{REF} can be any value between the supply rails.

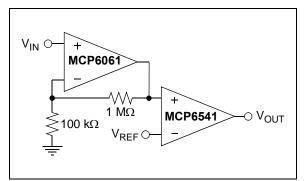


FIGURE 4-10: Precision, Non-inverting Comparator.

5.0 DESIGN AIDS

Microchip provides the basic design tools needed for the MCP6061/2/4 family of op amps.

5.1 SPICE Macro Model

The latest SPICE macro model for the MCP6061/2/4 op amps is available on the Microchip web site at www.microchip.com. The model was written and tested in official Orcad (Cadence) owned PSPICE. For the other simulators, it may require translation.

The model covers a wide aspect of the op amp's electrical specifications. Not only does the model cover voltage, current, and resistance of the op amp, but it also covers the temperature and noise effects on the behavior of the op amp. The model has not been verified outside of the specification range listed in the op amp data sheet. The model behaviors under these conditions can not be guaranteed that it will match the actual op amp performance.

Moreover, the model is intended to be an initial design tool. Bench testing is a very important part of any design and cannot be replaced with simulations. Also, simulation results using this macro model need to be validated by comparing them to the data sheet specifications and characteristic curves.

5.2 FilterLab[®] Software

Microchip's FilterLab[®] software is an innovative software tool that simplifies analog active filter (using op amps) design. Available at no cost from the Microchip web site at www.microchip.com/filterlab, the FilterLab design tool provides full schematic diagrams of the filter circuit with component values. It also outputs the filter circuit in SPICE format, which can be used with the macro model to simulate actual filter performance.

5.3 Microchip Advanced Part Selector (MAPS)

MAPS is a software tool that helps semiconductor professionals efficiently identify Microchip devices that fit a particular design requirement. Available at no cost from the Microchip website at www.microchip.com/ maps, the MAPS is an overall selection tool for Microchip's product portfolio that includes Analog, Memory, MCUs and DSCs. Using this tool you can define a filter to sort features for a parametric search of devices and export side-by-side technical comparison reports. Helpful links are also provided for Data Sheets, purchase, and sampling of Microchip parts.

5.4 Analog Demonstration and Evaluation Boards

Microchip offers a broad spectrum of Analog Demonstration and Evaluation Boards that are designed to help you achieve faster time to market. For a complete listing of these boards and their corresponding user's guides and technical information, visit the Microchip web site at www.microchip.com/ analogtools.

Some boards that are especially useful are:

- MCP6XXX Amplifier Evaluation Board 1
- MCP6XXX Amplifier Evaluation Board 2
- MCP6XXX Amplifier Evaluation Board 3
- MCP6XXX Amplifier Evaluation Board 4
- Active Filter Demo Board Kit
- 5/6-Pin SOT-23 Evaluation Board, P/N VSUPEV2
- 8-Pin SOIC/MSOP/TSSOP/DIP Evaluation Board, P/N SOIC8EV
- 14-Pin SOIC/TSSOP/DIP Evaluation Board, P/N SOIC14EV

5.5 Application Notes

The following Microchip Analog Design Note and Application Notes are available on the Microchip web site at www.microchip. com/appnotes and are recommended as supplemental reference resources.

- ADN003: "Select the Right Operational Amplifier for your Filtering Circuits", DS21821
- AN722: "Operational Amplifier Topologies and DC Specifications", DS00722
- AN723: "Operational Amplifier AC Specifications and Applications", DS00723
- AN884: "Driving Capacitive Loads With Op Amps", DS00884
- AN990: "Analog Sensor Conditioning Circuits An Overview", DS00990
- AN1177: "Op Amp Precision Design: DC Errors", DS01177
- AN1228: "Op Amp Precision Design: Random Noise", DS01228
- AN1332: "Current Sensing Circuit Concepts and Fundamentals", DS01332

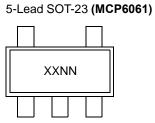
These application notes and others are listed in the design guide:

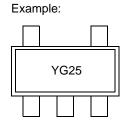
• "Signal Chain Design Guide", DS21825

NOTES:

6.0 PACKAGING INFORMATION

6.1 Package Marking Information





8-Lead SOIC (150 mil) (MCP6061, MCP6062)





8-Lead 2x3 TDFN (MCP6061, MCP6062)

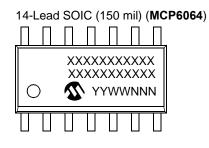
0	XXX	
	YWW	
	NN	
0		

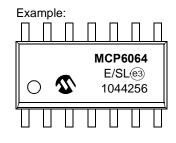
_	
Exam	nle:
	p.o.

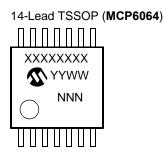
		AHC	
		/ 10	
		044	
		25	
	0	-	
- 1			

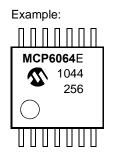
Legend:	XXX Y YY WW NNN (e3) *	Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.
I	be carried	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available s for customer-specific information.

Package Marking Information (Continuation)



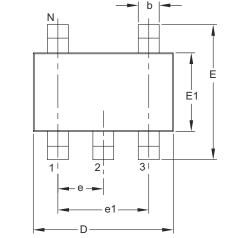


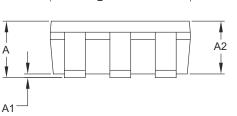


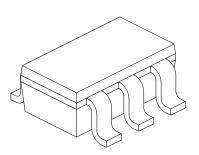


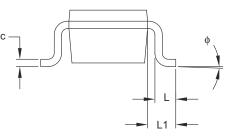
5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging









	Units	MILLIMETERS		
	Dimension Limits	MIN	NOM	MAX
Number of Pins	N		5	
Lead Pitch	e		0.95 BSC	
Outside Lead Pitch	e1		1.90 BSC	
Overall Height	A	0.90	-	1.45
Molded Package Thickness	A2	0.89	-	1.30
Standoff	A1	0.00	-	0.15
Overall Width	E	2.20	-	3.20
Molded Package Width	E1	1.30	-	1.80
Overall Length	D	2.70	-	3.10
Foot Length	L	0.10	-	0.60
Footprint	L1	0.35	-	0.80
Foot Angle	φ	0°	-	30°
Lead Thickness	С	0.08	-	0.26
Lead Width	b	0.20	_	0.51

Notes:

1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.

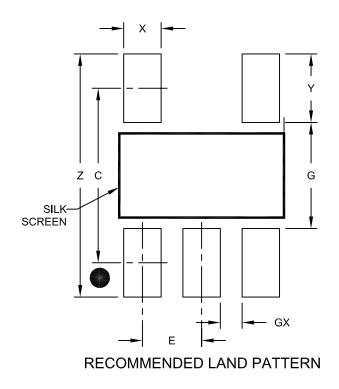
2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-091B

5-Lead Plastic Small Outline Transistor (OT) [SOT-23]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



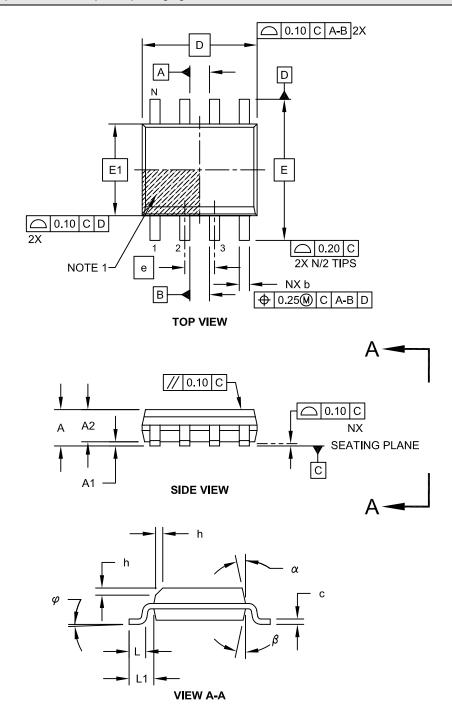
	MILLIMETERS			
Dimension	Limits	MIN	NOM	MAX
Contact Pitch	E	0.95 BSC		
Contact Pad Spacing	С		2.80	
Contact Pad Width (X5)	X			0.60
Contact Pad Length (X5)				1.10
Distance Between Pads	G	1.70		
Distance Between Pads		0.35		
Overall Width	Z			3.90

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2091A



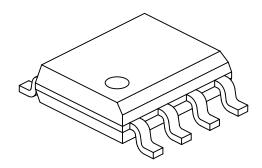
8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

Microchip Technology Drawing No. C04-057C Sheet 1 of 2

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Units		N	MILLIMETERS			
Dimension Limits		MIN	NOM	MAX		
Number of Pins	Ν	8				
Pitch	е		1.27 BSC			
Overall Height	А	-	-	1.75		
Molded Package Thickness	A2	1.25	-	-		
Standoff §	A1	0.10	-	0.25		
Overall Width	E	6.00 BSC				
Molded Package Width	E1	3.90 BSC				
Overall Length	D	4.90 BSC				
Chamfer (Optional)	h	0.25 - 0.50				
Foot Length	L	0.40 1.2				
Footprint	L1	1.04 REF				
Foot Angle	φ	0° - 8°				
Lead Thickness	С	0.17 - 0.2		0.25		
Lead Width	b	0.31 - 0.51				
Mold Draft Angle Top	α	5° - 15°				
Mold Draft Angle Bottom	β	5° - 15°				

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. § Significant Characteristic

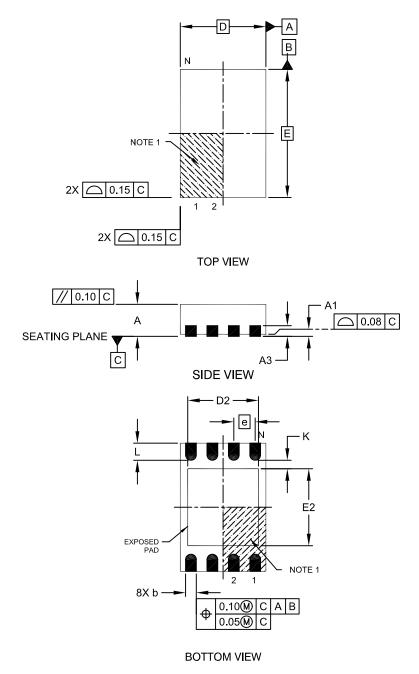
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

8-Lead Plastic Dual Flat, No Lead Package (MN) - 2x3x0.75mm Body [TDFN]

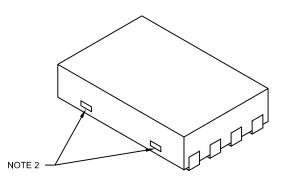
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-129C

8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75mm Body [TDFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS			
Dimonsion	Units Dimension Limits		NOM	MAX
		MIN		IVIAA
Number of Pins	N		8	
Pitch	е		0.50 BSC	
Overall Height	Α	0.70	0.75	0.80
Standoff	A1	0.00	0.02	0.05
Contact Thickness	A3	0.20 REF		
Overall Length	D	2.00 BSC		
Overall Width	E	3.00 BSC		
Exposed Pad Length	D2	1.20 - 1.60		
Exposed Pad Width	E2	1.20	-	1.60
Contact Width	b	0.20 0.25 0.30		0.30
Contact Length	L	0.25 0.30 0.45		
Contact-to-Exposed Pad	K	0.20	-	-

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

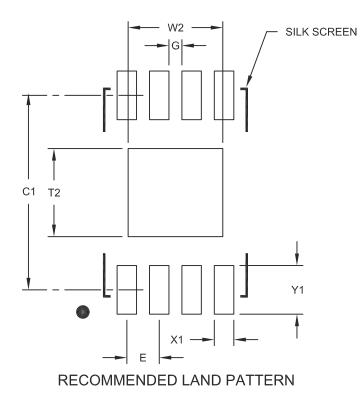
- 2. Package may have one or more exposed tie bars at ends.
- 3. Package is saw singulated
- 4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-129C Sheet 2 of 2

8-Lead Plastic Dual Flat, No Lead Package (MN) – 2x3x0.75 mm Body [TDFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units		MILLIMETERS			
Dimensi	Dimension Limits		NOM	MAX		
Contact Pitch	E	0.50 BSC				
Optional Center Pad Width	W2	1.46				
Optional Center Pad Length	T2	1.36				
Contact Pad Spacing	C1	3.00				
Contact Pad Width (X8)	X1	0.30				
Contact Pad Length (X8)	Y1			0.75		
Distance Between Pads	G	0.20				

Notes:

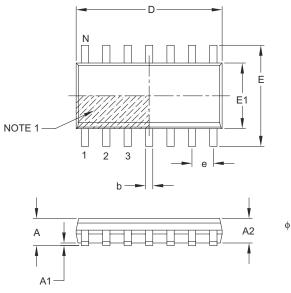
1. Dimensioning and tolerancing per ASME Y14.5M

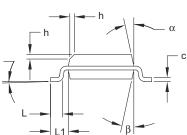
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2129A

14-Lead Plastic Small Outline (SL) – Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





	Units		MILLIMETERS			
	Dimension Limits		NOM	MAX		
Number of Pins	N	14				
Pitch	e		1.27 BSC			
Overall Height	A	-	-	1.75		
Molded Package Thickness	A2	1.25	-	-		
Standoff §	A1	0.10	-	0.25		
Overall Width	E	6.00 BSC				
Molded Package Width	E1	3.90 BSC				
Overall Length	D	8.65 BSC				
Chamfer (optional)	h	0.25 – 0.50				
Foot Length	L	0.40	-	1.27		
Footprint	L1	1.04 REF				
Foot Angle	φ	0° – 8°		8°		
Lead Thickness	С	0.17 – 0.25		0.25		
Lead Width	b	0.31 – 0.51		0.51		
Mold Draft Angle Top	α	5° – 15°				
Mold Draft Angle Bottom	β	5°	_	15°		

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. § Significant Characteristic.

3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15 mm per side.

4. Dimensioning and tolerancing per ASME Y14.5M.

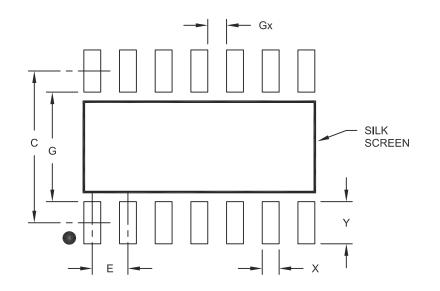
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-065B

14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	Units		MILLIMETERS			
Dimension	Dimension Limits		NOM	MAX		
Contact Pitch	E		1.27 BSC			
Contact Pad Spacing	С	5.40				
Contact Pad Width	Х			0.60		
Contact Pad Length	Y	1.50				
Distance Between Pads	Gx	0.67				
Distance Between Pads	G	3.90				

Notes:

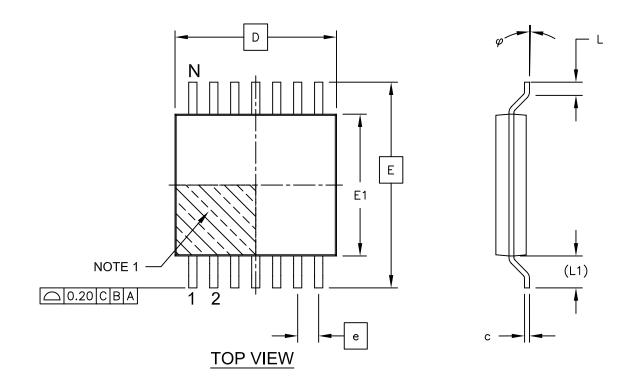
1. Dimensioning and tolerancing per ASME Y14.5M

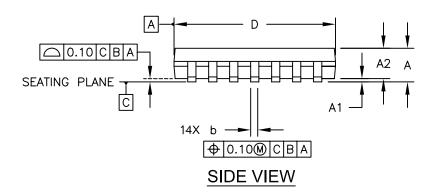
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2065A

14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

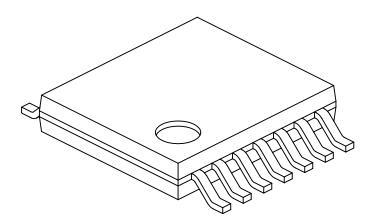




Microchip Technology Drawing C04-087C Sheet 1 of 2

14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS			
Dimension	Dimension Limits		NOM	MAX
Number of Pins	N	14		
Pitch	е		0.65 BSC	
Overall Height	A	-	-	1.20
Molded Package Thickness	A2	0.80	1.00	1.05
Standoff	A1	0.05 -		0.15
Overall Width	E	6.40 BSC		
Molded Package Width	E1	4.30 4.40 4.50		
Molded Package Length	D	4.90 5.00 5.10		
Foot Length	L	0.45	0.60	0.75
Footprint	(L1)	1.00 REF		
Foot Angle	φ	0° - 8°		8°
Lead Thickness	С	0.09 - 0.20		0.20
Lead Width	b	0.19	-	0.30

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

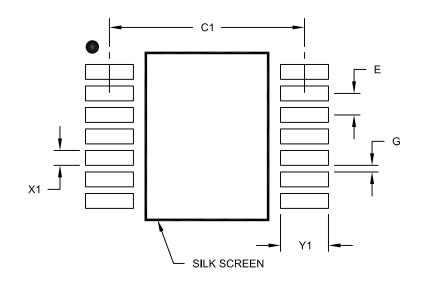
- 2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 3. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-087C Sheet 2 of 2

14-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	Units		MILLIMETERS			
Dimension	Dimension Limits		NOM	MAX		
Contact Pitch	E	0.65 BSC				
Contact Pad Spacing	C1	5.90				
Contact Pad Width (X14)	X1	0.4		0.45		
Contact Pad Length (X14)	Y1			1.45		
Distance Between Pads	G	0.20				

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2087A

APPENDIX A: REVISION HISTORY

Revision B (December 2010)

The following is the list of modifications:

- 1. Added new SOT-23-5 package type for MCP6061 device.
- 2. Corrected Figures 2-13, 2-22, 2-23, 2-24 and 2-28 in Section 2.0 "Typical Performance Curves".
- 3. Modified Table 3-1 to show the pin column for MCP6061, SOT-23-5 package.
- 4. Updated Section 4.1.2 "Input Voltage Limits".
- 5. Added Section 4.1.3 "Input Current Limits".
- 6. Added new document item in Section 5.5 "Application Notes".
- 7. Updated the package markings information and drawings.
- 8. Updated the Product Identification System page.

Revision A (June 2009)

• Original Release of this Document.

NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

Device Te	emperature Pa Range	ackage	a)	mples: MCP6061T-E/OT:	Tape and Reel, 5LD SOT-23 pkg
			b)	MCP6061-E/SN:	8LD SOIC pkg
Device:	MCP6061: MCP6061T:	Single Op Amp Single Op Amp (Tape and Reel)	c)	MCP6061T-E/SN:	Tape and Reel, 8LD SOIC pkg
	MCP6062: MCP6062T:	(SOIC, SOT-23 and 2x3 TDFN) Dual Op Amp Dual Op Amp (Tape and Reel)	d)	MCP6061T-E/MNY:	Tape and Reel, 8LD 2x3 TDFN pkg
	MCP6064:	(SOIC and 2x3 TDFN) Quad Op Amp	a)	MCP6062-E/SN:	8LD SOIC pkg
	MCP6064T:	Quad Op Amp (Tape and Reel) (SOIC and TSSOP)	b)	MCP6062T-E/SN:	Tape and Reel, 8LD SOIC pkg
Temperature Rang	ge: E = -40°C t	o +125°C	c)	MCP6062T-E/MNY:	Tape and Reel 8LD 2x3 TDFN pkg
			a)	MCP6064-E/SL:	14LD SOIC pkg
Package:	OT = Plastic	tic Dual Flat, No Lead, (2x3 TDFN) 8-lead Small Outline Transistor (SOT-23), 5-lead SOIC (150 mil Body), 14-lead	b)	MCP6064T-E/SL:	Tape and Reel, 14LD SOIC pkg
	SN = Plastic	SOIC (150 mil Body), 14-lead SOIC, (150 mil Body), 8-lead TSSOP (4.4mm Body), 14-lead	c) d)	MCP6064-E/ST: MCP6064T-E/ST:	14LD TSSOP pkg Tape and Reel,
	* Y = Nickel pal	ladium gold manufacturing designator. Only TDFN package.	u)	WCF00041-E/31.	14LD TSSOP pkg

NOTES:

Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

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